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Boraten

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(54) **SEMICONDUCTOR CHIP STACK WITH LOCKING THROUGH VIAS**

2224/16145; H01L 2224/17181; H01L 2225/06513; H01L 2225/06517; H01L 2225/06541; H01L 25/0657; H01L 29/7827

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See application file for complete search history.

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(*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

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H01L 23/00	(2006.01)
H01L 25/00	(2006.01)

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(52) **U.S. Cl.**

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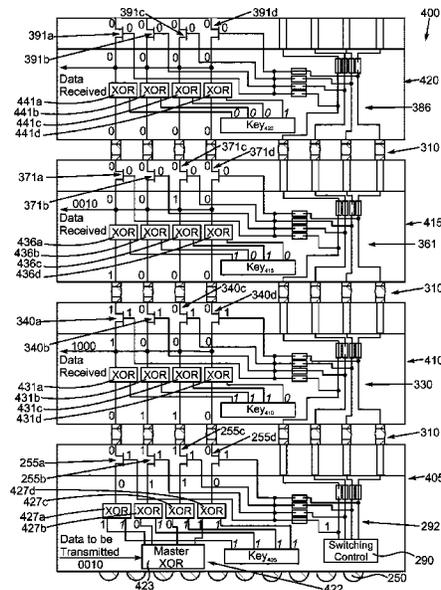
(57) **ABSTRACT**

Various semiconductor chips and chip stack arrangements are disclosed. In one aspect, a semiconductor chip stack is provided that includes a first semiconductor chip and a second semiconductor chip stacked on the first semiconductor chip. The first semiconductor chip includes a first logic layer and a first semiconductor layer on the first logic layer. The first semiconductor layer has plural first through-silicon transistors operable to selectively control the transmission of data from the first semiconductor chip to the second semiconductor chip and has plural first through-silicon vias to convey control signals to the second semiconductor chip.

(58) **Field of Classification Search**

CPC H01L 23/481; H01L 23/5252; H01L 23/5256; H01L 25/50; H01L 25/18; H01L 24/08; H01L 24/13; H01L 24/16; H01L 24/17; H01L 2224/06181; H01L 2224/08145; H01L 2224/13082; H01L 2224/131; H01L 2224/13147; H01L

20 Claims, 9 Drawing Sheets



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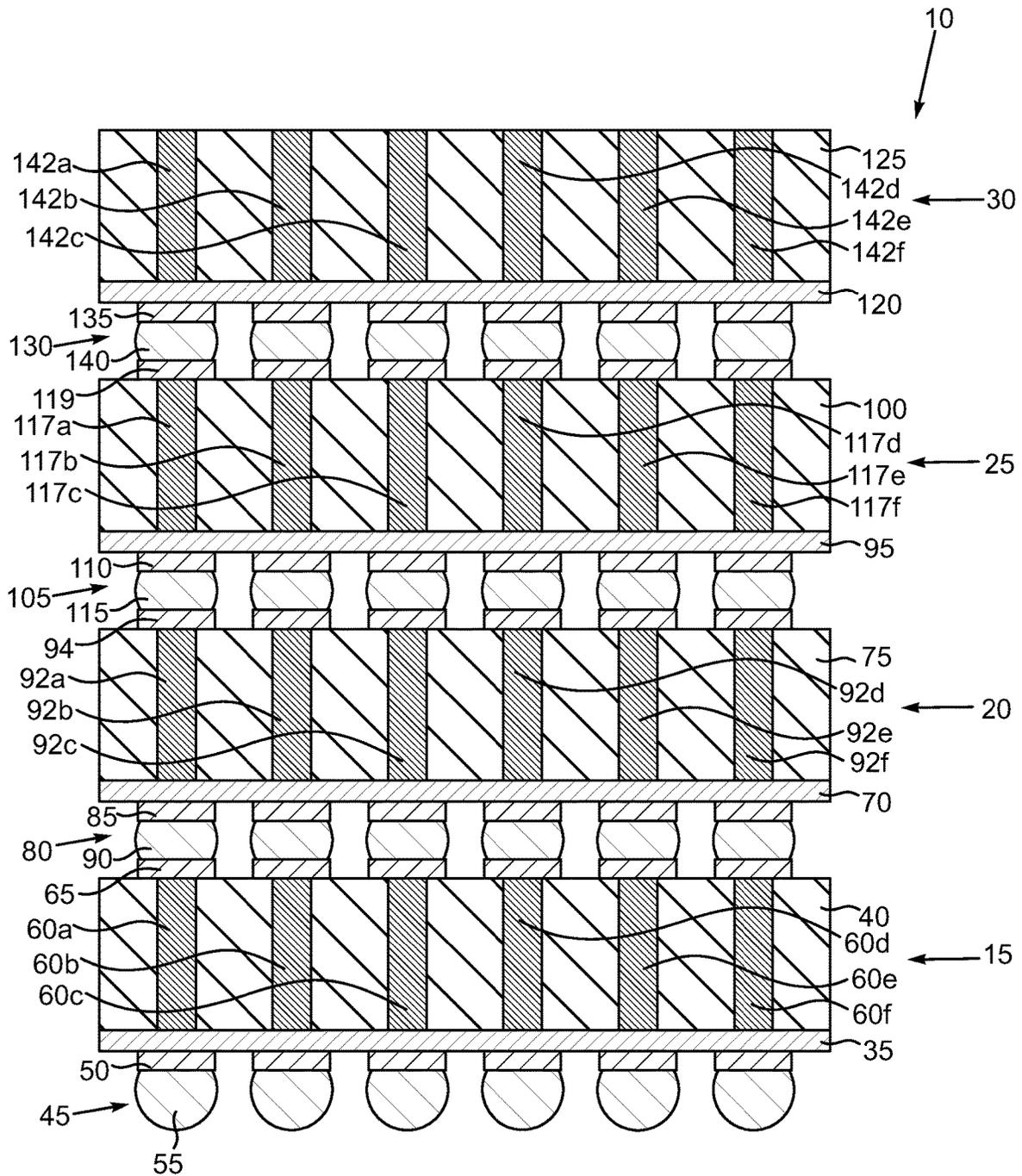


FIG. 1
(PRIOR ART)

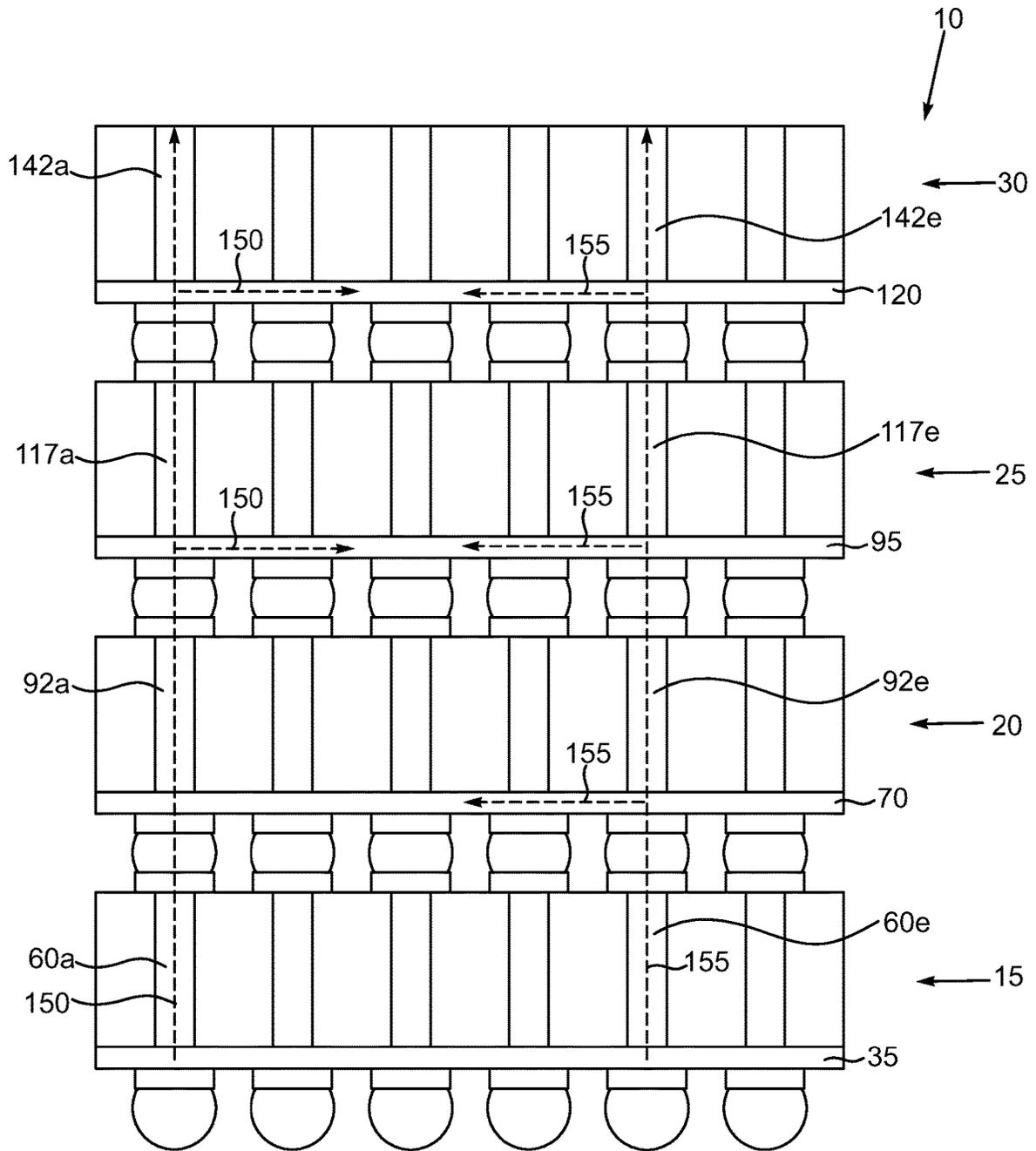


FIG. 2
(PRIOR ART)

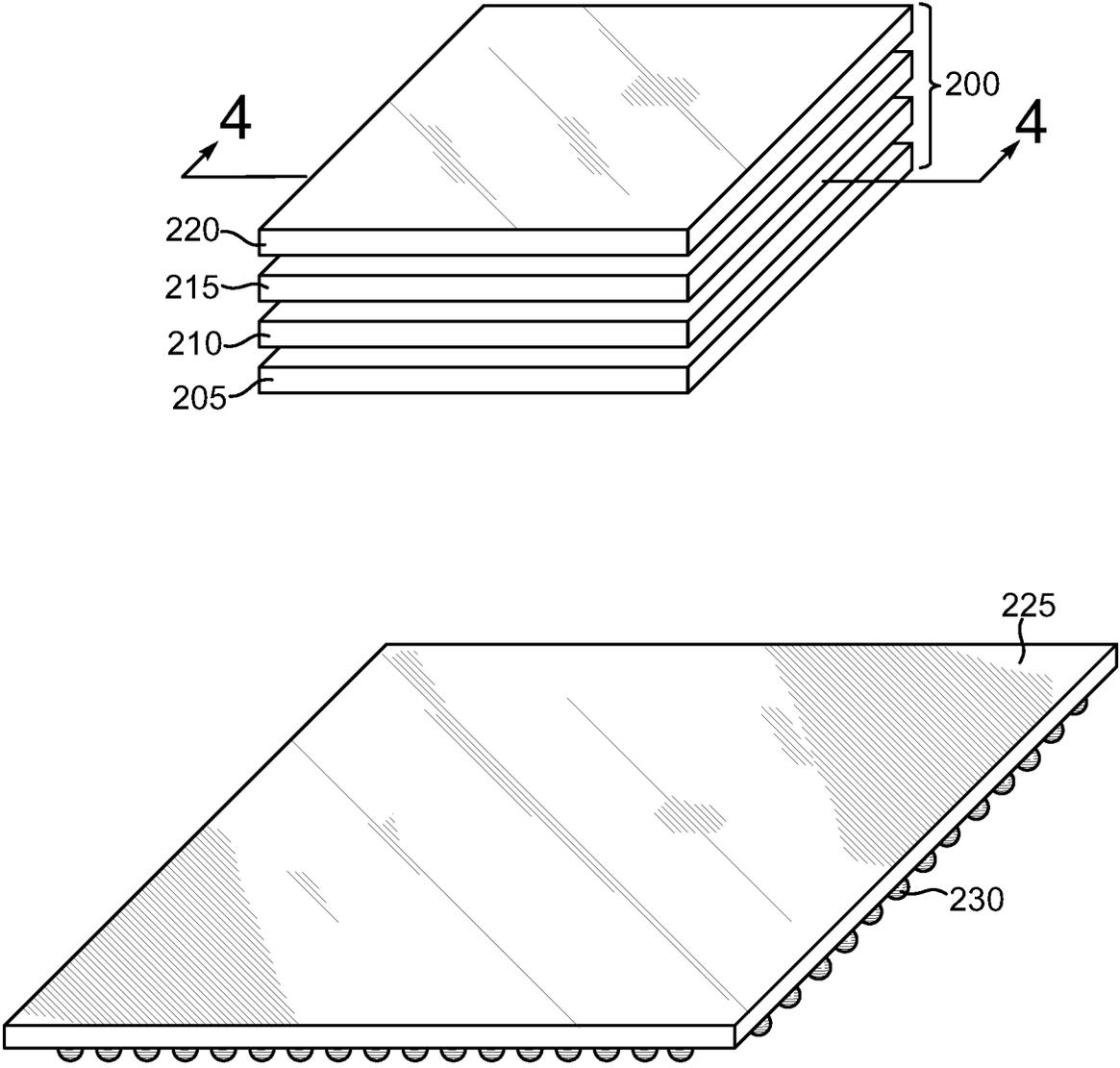


FIG. 3

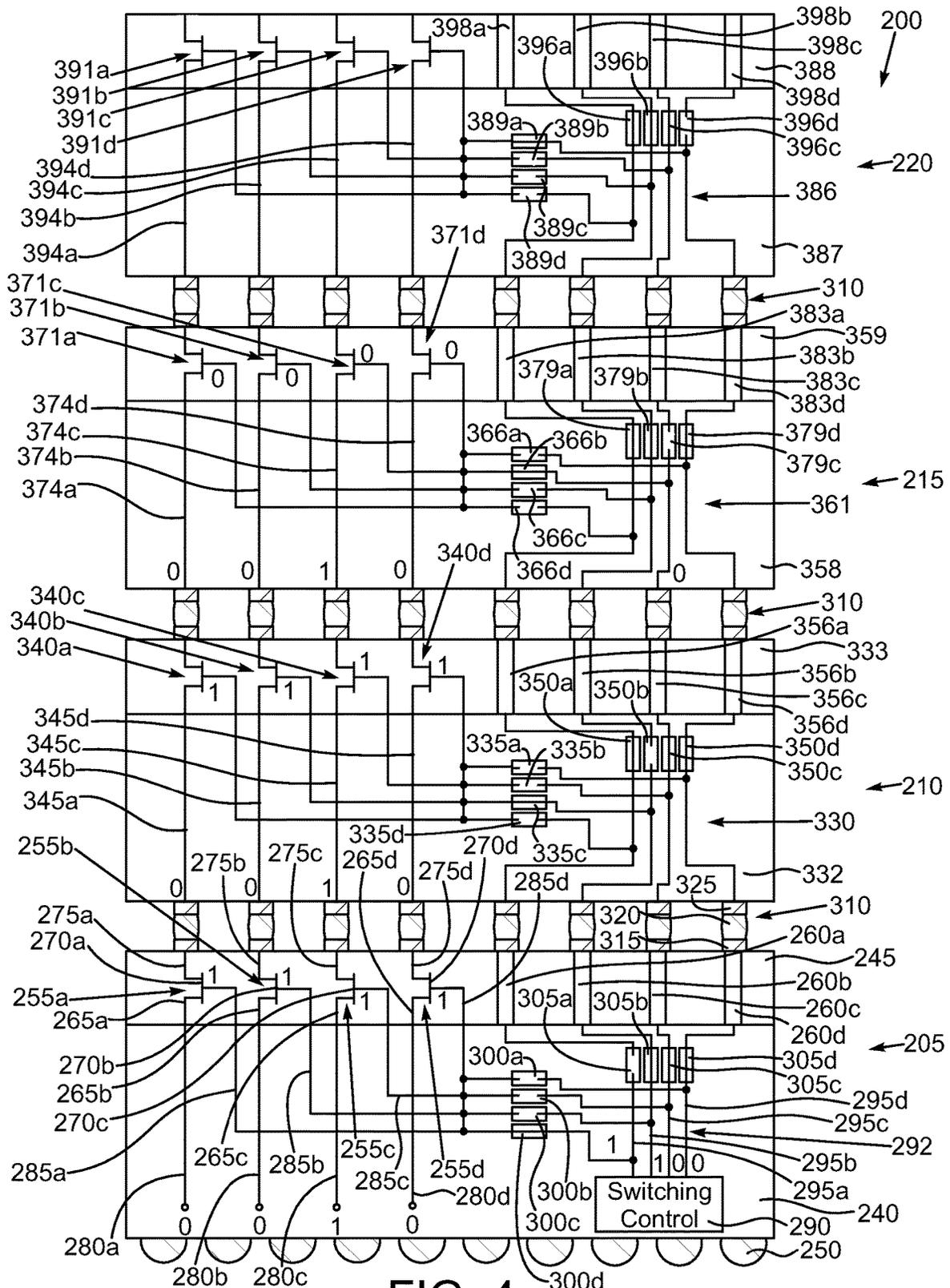


FIG. 4

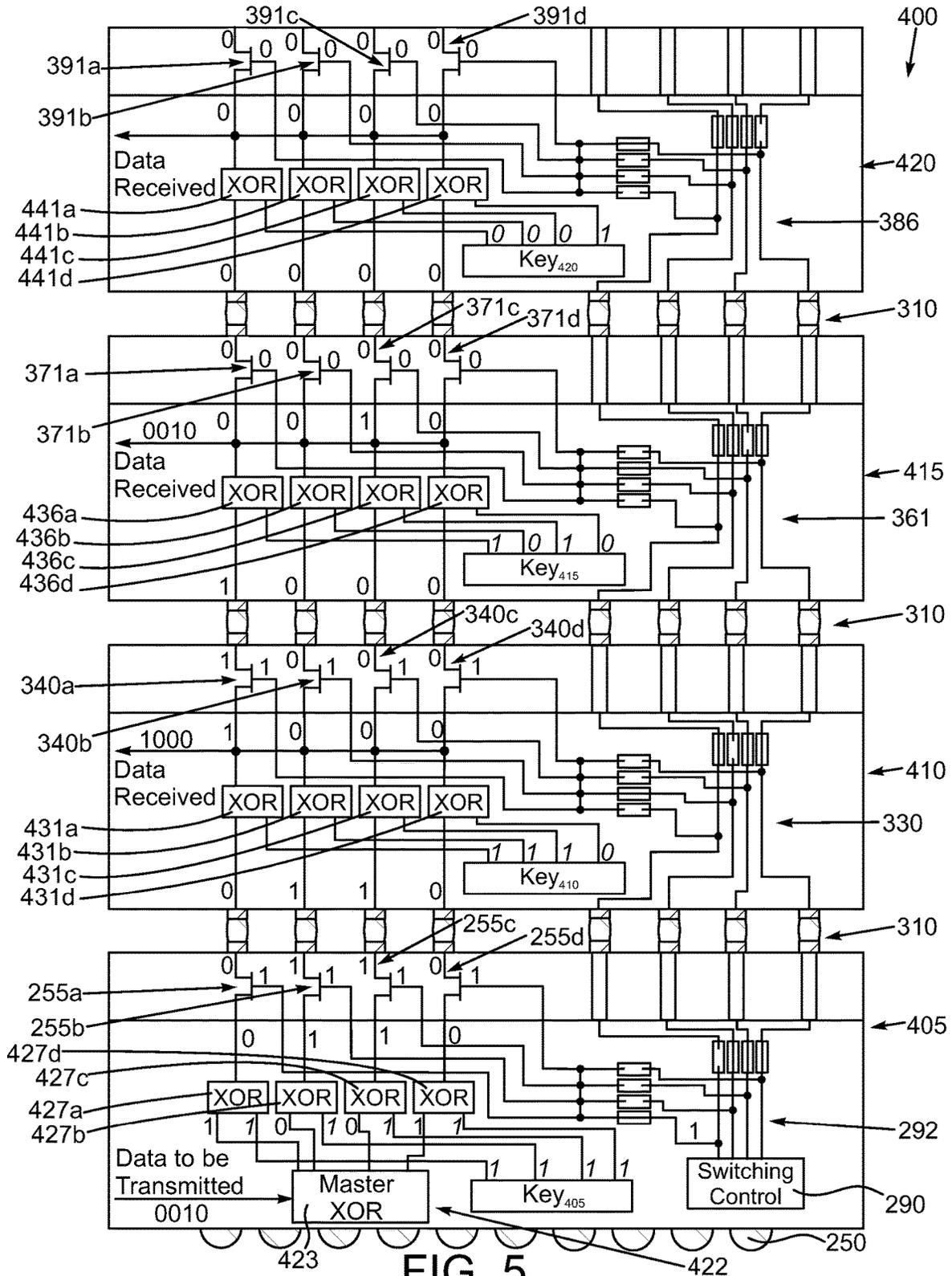


FIG. 5

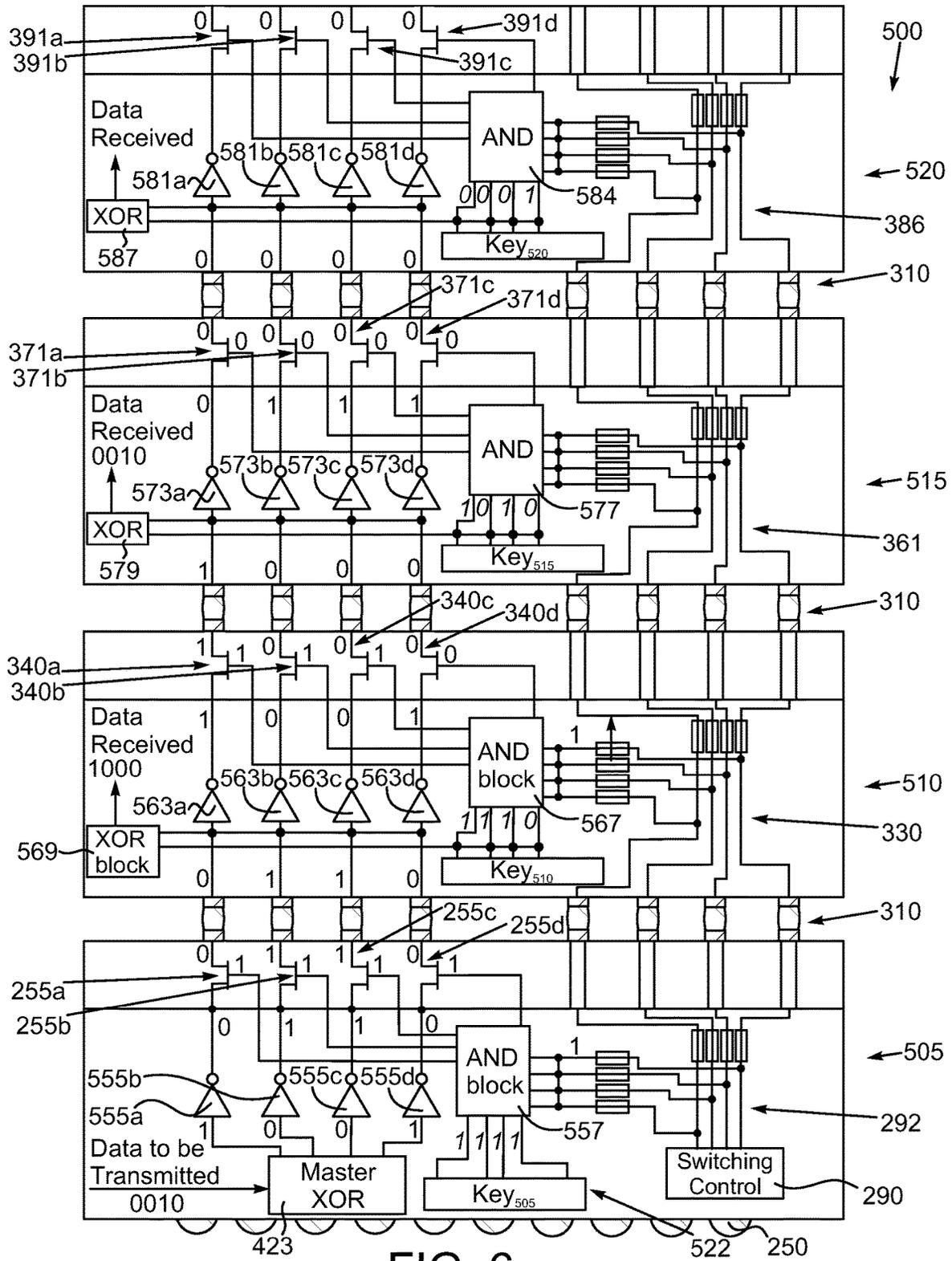


FIG. 6

Key₅₀₅ bits = 1111
Gate Control Signal
from Gate Control
Circuit 292 = 1

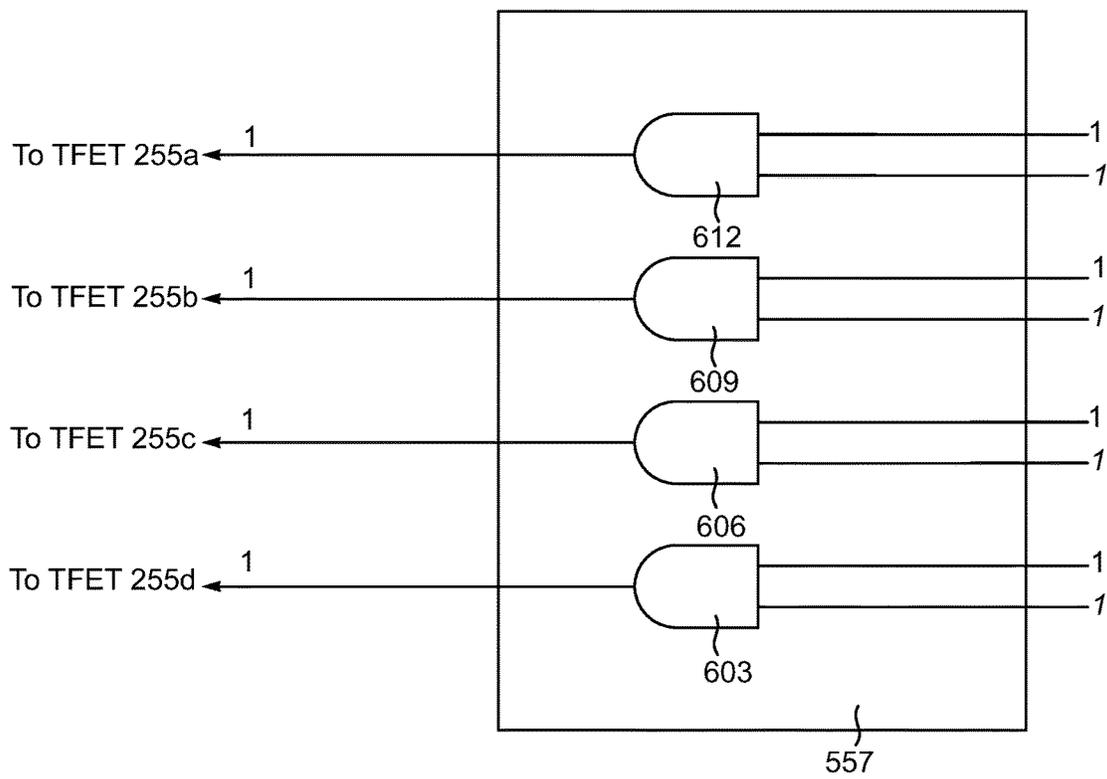


FIG. 7

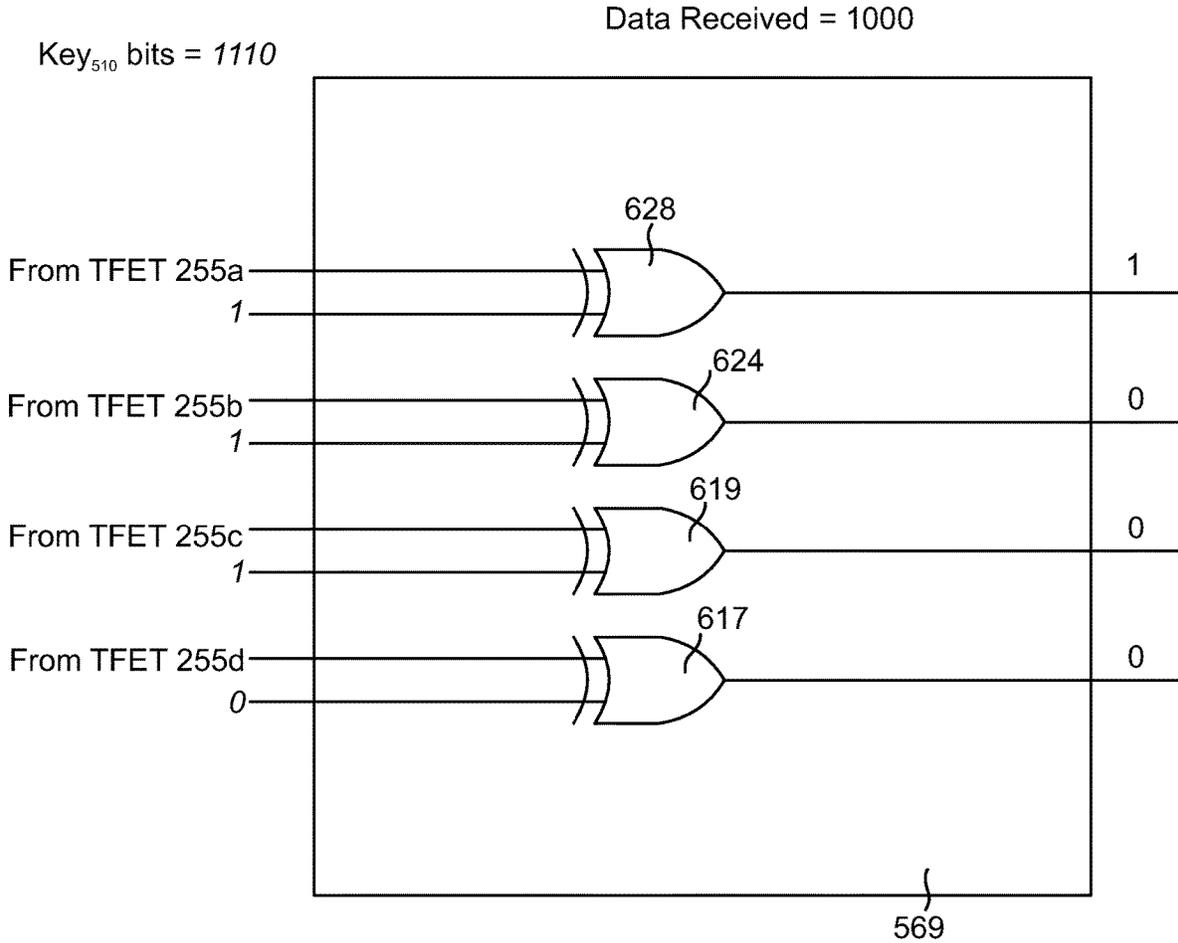


FIG. 8

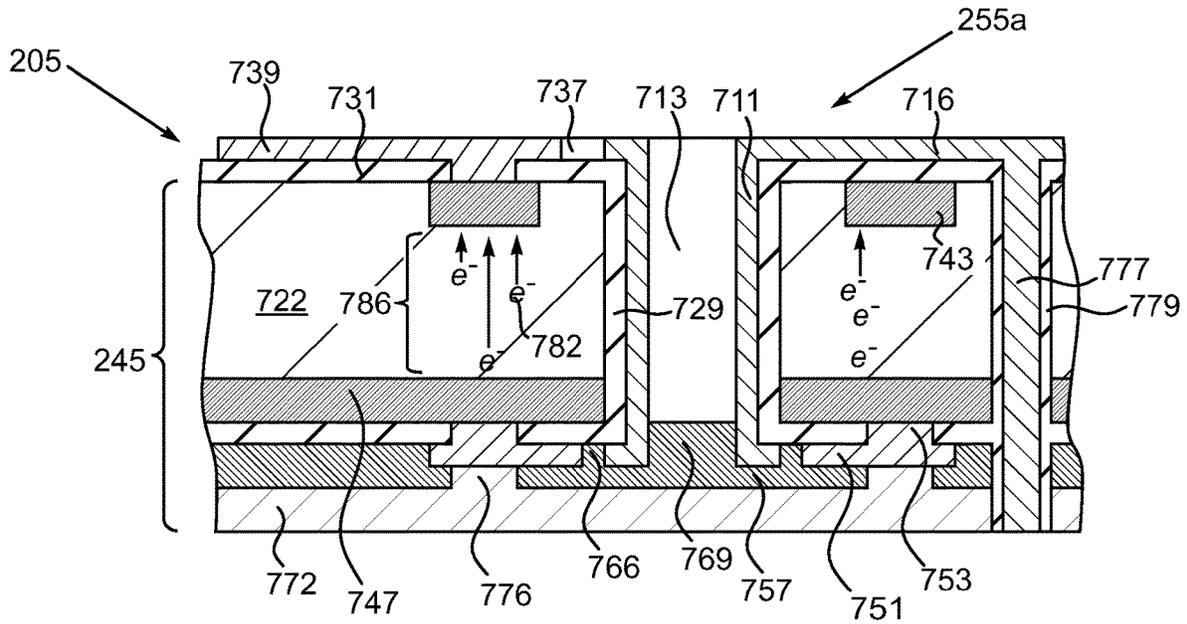


FIG. 9

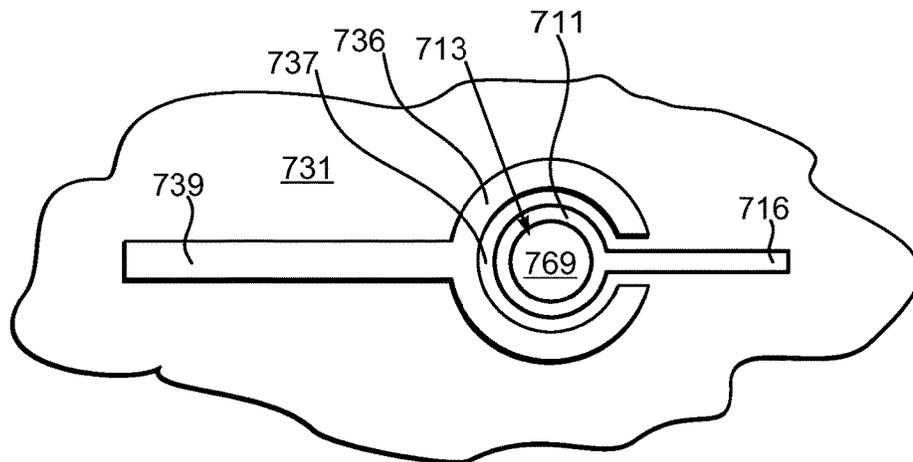


FIG. 10

SEMICONDUCTOR CHIP STACK WITH LOCKING THROUGH VIAS

BACKGROUND OF THE INVENTION

Many current integrated circuits are formed as multiple dice on a common wafer. After the basic process steps to form the circuits on the dice are complete, the individual die are singulated from the wafer. The singulated die are then usually mounted to structures, such as circuit boards, or packaged in some form of enclosure.

One frequently-used package consists of a substrate upon which a die is mounted. The upper surface of the substrate includes electrical interconnects. The die is manufactured with a plurality of bond pads. A collection of solder joints are provided between the bond pads of the die and the substrate interconnects to establish ohmic contact. After the die is mounted to the substrate, a lid is attached to the substrate to cover the die. Some conventional integrated circuits, such as microprocessors, generate sizeable quantities of heat that must be transferred away to avoid device shutdown or damage. The lid serves as both a protective cover and a heat transfer pathway.

Stacked dice arrangements involve placing or stacking one or more semiconductor chips on a base semiconductor chip. In some conventional variants, the base semiconductor chip is a high heat dissipating device, such as a microprocessor. The stacked chips are sometimes memory devices. The semiconductor chips in the stack often include through-silicon vias (TSVs) to pass power, ground and signals from one semiconductor chip to the next. In a typical conventional semiconductor chip stack, the TSVs in one chip are vertically aligned with the TSVs in the next chip and so on, such that the TSVs function like a data bus.

BRIEF DESCRIPTION OF THE DRAWINGS

The foregoing and other advantages of the invention will become apparent upon reading the following detailed description and upon reference to the drawings in which:

FIG. 1 is a schematic sectional view of an exemplary conventional semiconductor chip stack;

FIG. 2 is the schematic sectional view of the exemplary conventional semiconductor chip stack of FIG. 1 but with signal depiction;

FIG. 3 is a partially exploded pictorial view of an exemplary new chip stack arrangement;

FIG. 4 is a schematic sectional view of FIG. 3 taken at section 4-4;

FIG. 5 is a schematic sectional view like FIG. 4, but of an alternate exemplary arrangement of a chip stack arrangement;

FIG. 6 is a schematic sectional view like FIG. 5, but of another alternate exemplary arrangement of a chip stack arrangement;

FIG. 7 is a schematic view of an exemplary AND block;

FIG. 8 is a schematic view of an exemplary XOR block;

FIG. 9 is a sectional view of an exemplary through-silicon field effect transistor; and

FIG. 10 is a plan view of the exemplary through-silicon field effect transistor.

DETAILED DESCRIPTION

The designs for modern semiconductor chips are created using computer tools to generate a complex data file called a "tapeout". Where the creator of the tapeout does not

fabricates its own chips, the tapeouts are sent to third party fabricators that do the actual semiconductor chip fabrication. It is possible for a nefarious actor to intercept the tapeout data and inject unwanted and potentially malicious circuitry into the design that would cause the manufactured chip to malfunction, reveal secret information, or otherwise fail to meet specifications. Stacked chip designs represent a variant of this risk. For a given chip stack, there is the possibility that the chips of the stack are manufactured by multiple different fabs. One or more of the third-party supplied semiconductor chips can contain malicious circuitry. Conventional chip stack designs typically use TSVs in each semiconductor chip. Together, these TSVs act like a data bus, which means that data sent from one semiconductor chip to another semiconductor chip in the stack can be observed by all the semiconductor chips in the stack. This can be a problem where one of the semiconductor chips includes malicious circuitry capable of snooping on the data flowing in the stack.

The disclosed arrangements provide chip stacking with compartmentalized data flow. Data sent from one chip to another is prevented from flowing to various other semiconductor chips in the stack. In another arrangement, data destined for a particular semiconductor chip is encrypted before transmission and then decrypted at the destination chip. Intervening semiconductor chips will not see encrypted data, not the true data. Various encryption/decryption circuits are disclosed. Through-silicon field effect transistors are used in lieu of traditional TSVs for the data flow. Additional details will now be described.

In accordance with one aspect of the present invention, a semiconductor chip stack is provided that includes a first semiconductor chip and a second semiconductor chip stacked on the first semiconductor chip. The first semiconductor chip includes a first logic layer and a first semiconductor layer on the first logic layer. The first semiconductor layer has plural first through-silicon transistors operable to selectively control the transmission of data from the first semiconductor chip to the second semiconductor chip and has plural first through-silicon vias to convey control signals to the second semiconductor chip.

In accordance with another aspect of the present invention, an apparatus is provided that includes a first semiconductor chip operable to have a second semiconductor chip stacked thereon. The first semiconductor chip includes a first logic layer and a first semiconductor layer on the first logic layer. The first semiconductor layer has plural first through-silicon transistors operable to selectively control the transmission of data from the first semiconductor chip to the second semiconductor chip and has plural first through-silicon vias to convey control signals to the second semiconductor chip. The first semiconductor chip includes an encryption circuit operable to encrypt the data.

In accordance with another aspect of the present invention, a method of manufacturing is provided that includes stacking a first semiconductor chip on a second semiconductor chip. The second semiconductor chip includes a first logic layer and a first semiconductor layer on the first logic layer. The first semiconductor layer has plural first through-silicon transistors operable to selectively control the transmission of data from the second semiconductor chip to the first semiconductor chip and has plural first through-silicon vias to convey control signals to the first semiconductor chip.

In the drawings described below, reference numerals are generally repeated where identical elements appear in more than one figure. Turning now to the drawings, and in

particular to FIG. 1, therein is shown a sectional view of an exemplary conventional chip stack 10 that includes four semiconductor chips 15, 20, 25 and 30. The bottommost semiconductor chip 15 includes a back end of line or BEOL 35 which includes the various logic structures that make up the functionality of the semiconductor chip 15 as well as plural metallization layers that enable the logic devices of the BEOL 35 to connect to other conductor structures. In addition, the semiconductor chip 15 includes a bulk silicon portion 40 to interface electrically with another structure such, the semiconductor chip 20. To electrically interface with an underlying structure, such as a circuit board (not shown), the semiconductor chip 15 includes plural interconnects 45 which each consist of a bump pad 50 and a solder bump 55. To interface electrically with overlying structures, the bottommost semiconductor chip 15 includes plural through-silicon-vias 60a, 60b, 60c, 60d, 60e and 60f, which extend vertically through the bulk silicon portion 40. The TSVs 60a, 60b, 60c, 60d, 60e and 60f terminate at respective bump pads 65.

The semiconductor chip 20 similarly includes a BEOL 70, and a bulk silicon portion 75. In addition, the semiconductor chip 20 includes plural interconnects 80, which consist of a bump pad 85 and a solder bump 90. The solder bumps 90 are connected to respective of the bump pads 65 of the semiconductor chip 15. Like the semiconductor chip 15, the semiconductor chip 20 includes plural TSVs 92a, 92b, 92c, 92d, 92e and 92f. However, the TSVs 92a, 92b, 92c, 92d, 92e and 92f traverse the bulk silicon portion 75.

The semiconductor chip 25 similarly consists of a BEOL 95 and a bump silicon portion 100. In addition, the semiconductor chip 25 includes the plural interconnects 105 each of which consists of a bump pad 110 and a solder bump 115. Like the semiconductor chip 20, the semiconductor chip 25 includes plural TSVs 117a, 117b, 117c, 117d, 117e and 117f. However, the TSVs 117a, 117b, 117c, 117d, 117e and 117f traverse the bulk silicon portion 100. Finally, the semiconductor chip 30 consists of a BEOL 120 and a bump silicon portion 125. In addition, the semiconductor chip 30 includes the plural interconnects 130 each of which consists of a bump pad 135 and a solder bump 140. The topmost chip 30 also includes plural TSVs 142a, 142b, 142c, 142d, 142e and 142f, which traverse the bulk silicon portion 125.

The semiconductor chip 15 is operable to send data signals to the semiconductor chips 20, 25 and 30 and to receive data signals back from those same chips 20, 25 and 30. In this regard, a set of TSVs, such as the TSVs 60a, 92a, 117a and 142a, function as a data bus, another set of TSVs 60e, 92e, 117e and 142e function as another data bus and so on for the other TSVs of the semiconductor chips 15, 20, 25 and 30. While this has the advantage of providing relatively speedy pathways for the data signals flowing between the semiconductor chips 15, 20, 25 and 30, there are some pitfalls to be described in conjunction with FIG. 2.

Attention is now turned to FIG. 2, which is a sectional view like FIG. 1 but without cross-hatching so that the movement of data signals can be more easily illustrated and viewed. Assume for the purposes of this illustration that the semiconductor chip 15, and in particular the BEOL 35 thereof, transmits a data signal 150 that is intended for delivery to and use by the semiconductor chip 25. The data signal 150 is transmitted along the functional data bus consisting of the TSV 60a, the TSV 92a and ultimately to the BEOL 95 of the semiconductor chip 25. However, because of the bus-like nature of the TSVs 60a, 92a, 117a and 142a in the stack 10, the data signal 150 is also conveyed to the BEOL 120 of the semiconductor chip 30. Assume also for

this illustration, that the BEOL 35 of the semiconductor chip 15 conveys a data signal 155 that is intended for consumption by the semiconductor chip 30. In this regard, the data signal 155 is conveyed from the BEOL 35 through the functional bus consisting of the TSV 60e, the TSV 92e, the TSV 117e and ultimately to the BEOL 120 of the semiconductor chip 30. However, because of the bus-like nature of the TSVs 60a, 92a, 117a and 142a, 60e, 92e, 117e and 142e of the semiconductor chip stack 10, the data signal 155 is as noted also seen by the semiconductor chip 30 and the data signal 155, which is intended for consumption only by the semiconductor chip 30 is also seen by the semiconductor chips 20 and 25. A difficulty arises if one or more of the semiconductor chips 15, 20, 25 or 30 includes nefarious logic that is capable of snooping on the data signals that are not necessarily intended for a given chip. For example, since the semiconductor chip 30 is also a recipient of the data signal 150, if that semiconductor chip 30 is considered nefarious, there is a potential for unwanted snooping of the data signal 150. Similarly, if the semiconductor chips 20 and 25 are considered nefarious, they nevertheless are recipients of the data signal 155 that is ultimately intended only for the semiconductor chip 30.

FIG. 3 is a partially exploded pictorial view of an exemplary new arrangement of a chip stack 200 that includes semiconductor chips 205, 210, 215 and 220. The semiconductor chip stack 200 is configured to be mounted on another device such as the circuit board 225. The circuit board 225 can be a package substrate, a system board, a circuit card, a daughter card or other. To interface electrically with another device, the circuit board 225 can include plural interconnects 230, which can be the solder balls depicted or other types of interconnects such as pins, lands or others. The semiconductor chips 205, 210, 215 and 220 can be any of a variety of integrated circuits. A non-exhaustive list of examples includes processors, such as microprocessors, graphics processing units, accelerated processing units that combine aspects of both, memory devices, systems-on-chip, an application integrated specific circuit or other. In this illustrative arrangement, the semiconductor chip stack 200 includes the four semiconductor chips 205, 210, 215 and 220. However, the skilled artisan will appreciate that other than four chips can be used for the semiconductor chip stack 200 and any disclosed alternatives.

Additional details of the semiconductor chip stack 200 can be understood by referring now also to FIG. 4, which is a sectional-like view of FIG. 3 taken at section 4-4. FIG. 4 has attributes of a sectional view but various of the circuit structures within the semiconductor chips 205, 210, 215 and 220 are depicted schematically. The semiconductor chip 205 is the lowermost chip in the stack 200 and consists of a logic layer or BEOL 240 and a bulk semiconductor portion 245. Here, it should be understood that the BEOL 240 and the bulk semiconductor portion 245 are not depicted with accurate proportions in that the bulk semiconductor portion 245 in reality can be substantially thicker than the BEOL 240. The BEOL 240 includes plural interconnects 250, which can be solder balls, bumps, conductive pillars or other types of interconnect structures that are designed to make electrical connections to the circuit board 225 depicted in FIG. 3 or to some other semiconductor chip (not shown). The BEOL 240 includes various logic (not shown) that provides the basic functionality of the semiconductor chip 205. These so-called logic or IP blocks can include memory, arithmetic logic units, or virtually any other type of IP blocks. The BEOL 240 includes separate data pathways and control signal pathways. As noted above, in the conventional arrangement

depicted in FIGS. 1 and 2, a typical data pathway is a bus-like structure consisting of, for example, the stack of TSVs 60a, 92a, 117a and 142a. However, in this new illustrative arrangement depicted in FIGS. 3 and 4, the data pathways for a given chip such as the semiconductor chip 205 utilizes controlled switching to selectively pass or not pass data from the semiconductor chip 205 to other locations in the semiconductor chip stack 200. In this regard, the bulk semiconductor portion 245 includes plural through-silicon transistors 255a, 255b, 255c and 255d in lieu of regular TSVs. In this illustrative arrangement and the other disclosed arrangements, the through-silicon-transistors 255a, 255b, 255c and 255d are implemented as through-silicon field effect transistors (TFETs), and more particularly enhancement mode TFETs, but other through-silicon transistors could be used. Indeed, the term “through-silicon” as used herein is not limited to silicon, since other semiconductor materials, such as germanium or the like could be used for the semiconductor portion 245 and the other disclosed semiconductor portions. To provide control signal pathways, the bulk semiconductor portion 245 includes plural TSVs 260a, 260b, 260c and 260d. The TFETs 255a, 255b, 255c and 255d include respective sources 265a, 265b, 265c and 265d, respective gates 270a, 270b, 270c and 270d and respective drains 275a, 275b, 275c and 275d. The sources 265a, 265b, 265c and 265d are connected to respective data lines 280a, 280b, 280c and 280d of the BEOL 240. The data lines 280a, 280b, 280c and 280d are simply data conductors that are operable to convey data signals from elsewhere in the BEOL 240 to the sources 265a, 265b, 265c and 265d. The gates 270a, 270b, 270c and 270d are connected to respective control lines 285a, 285b, 285c and 285d of the BEOL 240, which are in turn connected to a switching control logic block 290 also of the BEOL 240. The switching control logic block 290 is operable to convey HIGH or LOW signals that are used to turn on or off the TFETs 255a, 255b, 255c and 255d as well as similar TFETs in the semiconductor chips 210, 215 and 220, which are discussed below. The switching control logic block 290 is connected and outputs to a gate control network 292. The gate control network 292 includes output lines 295a, 295b, 295c and 295d that are connected to the TSVs 260a, 260b, 260c and 260d, respectively, and commonly and in parallel to the control lines 285a, 285b, 285c and 285d. Note, however, that the control lines 285a, 285b, 285c and 285d of the gate control network 292 include respective programmable elements 300a, 300b, 300c and 300d. The arrangements described herein use antifuses as an example of a programmable element. However, the skilled artisan should appreciate that the following description is applicable to fuses, antifuses, ovonic devices, or like programmable elements. Three of the programmable elements, for example, programmable elements 300a, 300b and 300c, can be blown or otherwise programmed so that an on/off signal to the gates 270a, 270b, 270c and 270d is delivered via a particular control line such as, for example, the control line 285a since the programmable element 300d has not been blown. Of course, the same effect can be achieved by blowing programmable elements 300a, 300b and 300d while leaving programmable element 300c intact and thus gate control signals will be delivered to the gates 270a, 270b, 270c and 270d by way of the control line 285c and so on.

The output lines 295a, 295b, 295c and 295d of the gate control network 292 similarly include programmable elements 305a, 305b, 305c and 305d. By selectively blowing or otherwise programming one of the programmable elements 305a, 305b, 305c and 305d, a control signal from the

switching control logic block 290 can be prevented from propagating up through the semiconductor chip stack 200. For example, assume for the purposes of this discussion that the programmable element 305a has been blown. In this instance, a control signal on the output line 295a will be delivered to the gates 270a, 270b, 270c and 270d but be prevented from propagating up to the semiconductor chips 210, 215 and 220 since the programmable elements 305b, 305c and 305d have not been blown and thus the output lines 295b, 295c and 295d remain available for propagation of control signals to the semiconductor chips 210, 215 and 220.

Electrical communication between adjacent chips for the semiconductor chip stack 200, such as the semiconductor chips 205 and 210, can be by way of plural interconnects 310, which can consist of a conductor pad 315 on an underlying chip such as the semiconductor chip 205, a solder bump 320 connected to the lower pad 315 and an upper conductor pad 325 connected to the overlying chip, such as the semiconductor chip 210. Optionally, the interconnects 310 can consist of conductive pillars with or without solder caps, so-called hybrid bonds that involve the direct metallurgical connection of one conductor structure to another such as two copper pillars or other types of interconnects as desired.

The semiconductor chip 210 is the next higher chip in the stack 200 and consists of a BEOL 332 and a bulk semiconductor portion 333, which can be substantially similar to the BEOL 240 and the bulk semiconductor portion 245 of the semiconductor chip 205. The semiconductor chip 210 includes a gate control network 330, which can be substantially similar to the gate control network 292 in the semiconductor chip 205 and as described above. However, the gate control network 330 of the semiconductor chip 210 is connected to the TSVs 260a, 260b, 260c and 260d, and thus the switching control logic block 290, of the semiconductor chip 205 by way of the interconnects 310. The gate control network 330 includes plural programmable elements 335a, 335b, 335c and 335d that control the flow of gate control signals to respective TFETs 340a, 340b, 340c and 340d of the bulk semiconductor portion 333 of the semiconductor chip 210. The TFETs 340a, 340b, 340c and 340d can be substantially identical to the TFETs 255a, 255b, 255c and 255d in the semiconductor chip 205 and as described above, and for simplicity of illustration the gates, sources and drains of the TFETs 340a, 340b, 340c and 340d are not separately numbered. The TFETs 340a, 340b, 340c and 340d are connected to respective data lines 345a, 345b, 345c and 345d, which are in turn connected to the TFETs 255a, 255b, 255c and 255d by way of some of the interconnects 310. The gate control network 330 also includes plural programmable elements 350a, 350b, 350c and 350d that are selectively blown or not in order to pass or not pass control signals up through the semiconductor chip 210 to the overlying chip 215. Here, it is assumed for the purposes of this discussion that the programmable elements 335a, 335b and 335d have been blown but the programmable element 335c has not and thus gate control signals will be conveyed through the unblown programmable element 335c to provide gate control signals to the gates of the TFETs 340a, 340b, 340c and 340d. Similarly, it is assumed that the programmable elements 350a, 350c and 350d have not been blown but the programmable element 350b has been blown. The programmable elements 335a, 335b, 335c, 335d, 350a, 350b, 350c and 350d can be like the programmable elements 300a, 300b, 300c, 300d, 305a, 305b, 305c and 305d described

above. The semiconductor chip **210** includes plural TSVs **356a**, **356b**, **356c** and **356d** that are positioned in the bulk semiconductor portion **333**.

The semiconductor chip **215** is the next higher chip in the stack **200** and consists of a BEOL **358** and a bulk semiconductor portion **359**, which can be substantially similar to the BEOL **332** and the bulk semiconductor portion **333** of the semiconductor chip **210**. The semiconductor chip **215** includes a gate control network **361**, which can be substantially similar to the gate control network **292** in the semiconductor chip **205** and as described above. However, the gate control network **361** of the semiconductor chip **215** is connected to the TSVs **356a**, **356b**, **356c** and **356d** of the semiconductor chip **210** by way of the interconnects **310**. The gate control network **361** includes plural programmable elements **366a**, **366b**, **366c** and **366d** that control the flow of gate control signals to respective TFETs **371a**, **371b**, **371c** and **371d** of the bulk semiconductor portion **359** of the semiconductor chip **215**. The TFETs **371a**, **371b**, **371c** and **371d** can be substantially identical to the TFETs **255a**, **255b**, **255c** and **255d** in the semiconductor chip **205** and as described above. The TFETs **371a**, **371b**, **371c** and **371d** are connected to respective data lines **374a**, **374b**, **374c** and **374d**, which are in turn connected to the TFETs **340a**, **340b**, **340c** and **340d** of the semiconductor chip **210** by way of some of the interconnects **310**. The gate control network **361** also includes plural programmable elements **379a**, **379b**, **379c** and **379d** that are selectively blown or not in order to pass or not pass control signals up through the semiconductor chip **215** to the overlying chip **220**. Here, it is assumed for the purposes of this discussion that the programmable elements **366a**, **366c** and **366d** have been blown but the programmable element **366b** has not and thus gate control signals will be conveyed through the unblown programmable element **366b** to provide gate control signals to the gates of the TFETs **371a**, **371b**, **371c** and **371d**. Similarly, it is assumed that the programmable elements **379a**, **379b** and **379d** have not been blown but the programmable element **379c** has been blown. The programmable elements **366a**, **366b**, **366c**, **366d**, **379a**, **379b**, **379c** and **379d** can be like the programmable elements **300a**, **300b**, **300c**, **300d**, **305a**, **305b**, **305c** and **305d** described above. The semiconductor chip **215** includes plural TSVs **383a**, **383b**, **383c** and **383d** that are positioned in the bulk semiconductor portion **359**.

The semiconductor chip **220** is the topmost chip in the stack **200** and consists of a BEOL **387** and a bulk semiconductor portion **388**, which can be substantially similar to the BEOL **358** and the bulk semiconductor portion **359** of the semiconductor chip **215**. The semiconductor chip **220** includes a gate control network **386**, which can be substantially similar to the gate control network **292** in the semiconductor chip **205** and as described above. However, the gate control network **386** of the semiconductor chip **220** is connected to the TSVs **383a**, **383b**, **383c** and **383d** of the semiconductor chip **215** by way of the interconnects **310**. The gate control network **386** includes plural programmable elements **389a**, **389b**, **389c** and **389d** that control the flow of gate control signals to respective TFETs **391a**, **391b**, **391c** and **391d** in the bulk semiconductor portion **388** of the semiconductor chip **220**. The TFETs **391a**, **391b**, **391c** and **391d** can be substantially identical to the TFETs **255a**, **255b**, **255c** and **255d** in the semiconductor chip **205** and as described above. The TFETs **391a**, **391b**, **391c** and **391d** are connected to respective data lines **394a**, **394b**, **394c** and **394d**, which are in turn connected to the TFETs **371a**, **371b**, **371c** and **371d** of the semiconductor chip **215** by way of some of the interconnects **310**. The gate control network **386**

also includes plural programmable elements **396a**, **396b**, **396c** and **396d** that are selectively blown or not in order to pass or not pass control signals up through the semiconductor chip **215** to an overlying chip in the event the semiconductor chip **220** does have another semiconductor chip stacked thereon. Here, it is assumed for the purposes of this discussion that the programmable elements **389b**, **389c** and **389d** have been blown but the programmable element **389a** has not and thus gate control signals will be conveyed through the unblown programmable element **389a** to provide gate control signals to the gates of the transistors **391a**, **391b**, **391c** and **391d**. Similarly, it is assumed that the programmable elements **396a**, **396b** and **396c** have not been blown but the programmable element **379d** has been blown, although selective fusing and usage of the gate control network **386** is technically unnecessary where the semiconductor chip **220** does not have an overlying chip stacked thereon. The programmable elements **389a**, **389b**, **389c**, **389d**, **396a**, **396b**, **396c** and **396d** can be like the programmable elements **300a**, **300b**, **300c**, **300d**, **305a**, **305b**, **305c** and **305d** of the semiconductor chip **205** described above. The semiconductor chip **220** includes plural TSVs **398a**, **398b**, **398c** and **398d** that are positioned in the bulk semiconductor portion **388**, but which need not be used if there is no additional semiconductor chip stacked on the semiconductor chip **220**.

Exemplary data transmission for the semiconductor chip stack **200** will now be described. In this simple illustration, it is assumed that the semiconductor chip **205** will transmit a simple 4-bit number **0010** to the semiconductor chip **215**. Of course it should be understood that other than the number **0010** and other than 4-bit data handling could be used in this and the other disclosed arrangements. Initially, some bit of logic (not shown) in the semiconductor chip **205** generates the **0010** value and those individual bits are deployed on the data lines **280a**, **280b**, **280c** and **280d**. The switching control logic block **290** generates a logic 1 HIGH signal that is delivered to the gates **270a**, **270b**, **270c** and **270d** by way of the pathway associated with the un-blown programmable element **300d**. The logic 1 HIGH signals turn on the transistors **255a**, **255b**, **255c** and **255d** and the **0010** value is transmitted to the data lines **345a**, **345b**, **345c** and **345d** of the semiconductor chip **210**. However, the logic 1 HIGH signal delivered to the pathway that involves the programmable element **300d** is not propagated upward to the semiconductor chip **210** since the programmable element **305a** has been blown. However, the switching control logic block **290** does deliver gate control signals through the unblown programmable elements **305b**, **305c** and **305d** and ultimately the TSV's **260b**, **260c** and **260d**. In the semiconductor chip **210**, the logic 1 HIGH control signal delivered by way of the TSV **260b** is delivered to the gates of the transistors **340a**, **340b**, **340c** and **340d** by way of the pathway including the unblown programmable element **335c**. The logic HIGH 1 signals at the gates of the transistors **340a**, **340b**, **340c** and **340d** turns those transistors on and thus the digital value **0010** is transmitted from the semiconductor chip **210** to the data lines **374a**, **374b**, **374c** and **374d** of the semiconductor chip **215**. The switching control logic block **290** prevents the data values **0010** from being transmitted beyond the semiconductor chip **215**, i.e., to the semiconductor chip **220** by delivering a logic LOW 0 signal through the unblown programmable element **305c**, the TSV **260c**, the unblown programmable element **350c** of the semiconductor chip **210**, the TSV **356c** of the semiconductor chip **210** and ultimately to the pathway that includes the unblown programmable element **366b**. That logic 0 LOW signal is then conveyed to

the gates of the transistors **371a**, **371b**, **371c** and **371d** to thus turn those transistors off. In this way, the data value **0010** cannot be snooped on by the semiconductor chip **220**. This type of selective locking down of data pathways for the semiconductor chips **210**, **215** and **220** can be done whenever it is desired to limit the propagation of data to one or more semiconductor chips in the semiconductor chip stack **200**. For example, the semiconductor chip **205** can deliver a data value to the semiconductor chip **210**, and by shutting off the transistors **340a**, **340b**, **340c** and **340d**, that data value will not be propagated to the overlying chips **215** and **220**. Note that the foregoing data transmission can occur repeatedly for all sorts of data values and at speeds as fast or slow as the semiconductor chip architecture of the semiconductor chip stack **200** allows.

An alternate exemplary arrangement of a semiconductor chip stack **400** may be understood by referring now to FIG. **5**. FIG. **5** is a sectional-like schematic view similar to FIG. **4** and depicts the semiconductor chip stack **400** with semiconductor chips **405**, **410**, **415**, and **420**. The semiconductor chips **405**, **410**, **415** and **420** share many of the same attributes as the semiconductor chips **205**, **210**, **215** and **220** depicted in FIG. **4** and described above. In this regard, the semiconductor chip **405** includes the TFETs **255a**, **255b**, **255c** and **255d** as well as the interconnects **250**, the switching control logic block **290** and the gate control network **292**. The individual components of the gate control network **292** will not be shown in FIG. **5** for simplicity of illustration. The semiconductor chip **410** similarly includes the TFETs **340a**, **340b**, **340c** and **340d**, as well as the gate control network **330**, which like the gate control network **292**, will not include additional element numbering of the individual components for simplicity of illustration. The semiconductor chips **405** and **410** are electrically connected by way of the plural interconnects **310**. Similar pluralities of the interconnects **310** connect the semiconductor chips **410** and **415** and **415** and **420**, respectively. The semiconductor chip **415** similarly includes the TFETs **371a**, **371b**, **371c** and **371d**, as well as the gate control network **361**. Finally, the semiconductor chip **420** includes the TFETs **391a**, **391b**, **391c** and **391d** as well as the gate control network **386**.

In the arrangement of the semiconductor chip stack **200** depicted in FIG. **4** and described above, data is transferred through the stack **200** in the clear. However, the exemplary arrangement of the semiconductor chip stack **400** incorporates encryption schemes in order to encrypt data that is transferred from one chip to another. This illustrative encryption scheme will now be described. To simplify the discussion, a simple 4-bit data transmission scheme will be described. However, the skilled artisan will appreciate that other than 4-bit data can be handled with appropriate scaling up of the hardware to be described. The semiconductor chip **405** includes an encryption circuit **422** that includes a Master exclusive OR (XOR) block **423**, a 4-bit encryption key Key_{405} and four XOR gates **427a**, **427b**, **427c** and **427d**. The master XOR block **423** has 4 outputs, one for each of the XOR gates **427a**, **427b**, **427c** and **427d**. Because this is a 4-bit example, encryption Key_{405} includes 4 key bits. In this illustrative arrangement the Key_{405} bits are 1111, but they, and any other disclosed key bits, could be any 4-bit (or other length) number or word. Note that the Key_{405} bits 1111 are denoted in italics to distinguish them from the outputs of the master XOR block **423**. The encryption key Key_{405} (and any other disclosed keys) can be stored in firmware, non-volatile memory or other. While a 4-bit example is used for simplicity of illustration, the skilled artisan will appreciate that 32-bit, 64-bit, 128-bit, 256-bit or other length keys could be

used. The semiconductor chip **410** includes a four bit Key_{410} with four key bits 1110, the semiconductor chip includes a four bit key Key_{415} with key bits 1010 and the semiconductor chip **420** includes a four bit key Key_{420} with key bits 0001. Table 1 below summarizes the key bits for the keys Key_{405} , Key_{410} , Key_{415} and Key_{420} .

TABLE 1

Key	Key bits
Key_{405}	Key_{405} bits = 1111
Key_{410}	Key_{410} bits = 1110
Key_{415}	Key_{415} bits = 1010
Key_{420}	Key_{420} bits = 0001

The Key_{405} bits 1111 are delivered as inputs to the respective XOR gates **427a**, **427b**, **427c** and **427d**. The skilled artisan will recognize the following truth table for an XOR gate:

TABLE 2

Input A	Input B	Output
0	0	0
0	1	1
1	0	1
1	1	0

Assume for the purposes of this illustration that the 0010 data value is to be transmitted from the semiconductor chip **405** to the semiconductor chip **415**. The master XOR block **423** takes the input data value 0010 and performs XOR functions on that 0010 value to encrypt it into an encrypted 4-bit number that will be propagated through the semiconductor chip **410** and ultimately delivered to the semiconductor chip **415** where it will be decrypted back into the original data value 0010. Table 3 below lists the XOR operations performed by the XOR block **423** depending on the destination chip for the 0010 data value.

TABLE 3

Destination Chip	XOR Calculations
Chip 410	$0010 \oplus Key_{405}$ bits $\oplus Key_{410}$ bits
Chip 415	$0010 \oplus Key_{405}$ bits $\oplus Key_{410}$ bits $\oplus Key_{415}$ bits
Chip 420	$0010 \oplus Key_{405}$ bits $\oplus Key_{410}$ bits $\oplus Key_{415}$ bits $\oplus Key_{420}$ bits

where the \oplus symbol denotes an XOR operation. Thus where the destination chip is the semiconductor chip **415**, the XOR calculations for the data value of 0010 and the key bits listed in Table 1 above are

$$0010 \oplus 1111 \oplus 1110 \oplus 1010 = 1001 \tag{1}$$

where the XOR calculations are done on a per bit basis. Take for example the first XOR calculation $0010 \oplus 1111$. Here the first bit, bit 0, of the data value 0010 is XORed with the first bit, bit 1, of the Key_{405} bits, in other words $0 \oplus 1$, which yields a value of 1. Next, the second bit, bit 0, of the data value 0010 is XORed with the second bit, bit 1, of the Key_{405} bits, in other words $0 \oplus 1$, which yields a value of 1. Next, the third bit, bit 1, of the data value 0010 is XORed with the third bit, bit 1, of the Key_{405} bits, in other words $1 \oplus 1$, which yields a value of 0 and so on for the last bit, bit 0, of the data value 0010 and the last bit, bit 1, of the Key_{405} bits. Thus

$$0010 \oplus 1111 = 1101 \tag{2}$$

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That value 1101 from Equation (2) is next XORed with the Key₄₁₀ key bits 1110 on the same bit per bit basis to yield

$$1101 \oplus 1110 = 0011 \quad (3)$$

and then that value 0011 is next XORed with the Key₄₁₅ key bits 1010 on the same bit per bit basis to yield

$$0011 \oplus 1010 = 1001 \quad (4)$$

which, of course, is the result for Equation (1). The bit values 1001 from Equations (1) and (4) are delivered as inputs to the XOR gates 427a, 427b, 427c and 427d along with the Key₄₀₅ bits 1111 as shown in FIG. 5. The XOR gate 427a then performs an XOR operation on the bits 1 and 1 to yield a value of 0, the XOR gate 427b performs an XOR operation on the bits 0 and 1 to yield a value of 1 and so on for the other XOR gates 427c and 427d. Thus, the outputs of the XOR gates 427a, 427b, 427c and 427d are 0110 as shown at the inputs to the TFETs 255a, 255b, 255c and 255d, respectively. The gate control circuit 292 is outputting a logic 1 HIGH signal so the TFETs 255a, 255b, 255c and 255d are turned on and the encrypted value 0110 is passed to the semiconductor chip 410.

The semiconductor chip 410 includes the 4-bit encryption key Key₄₁₀ and four XOR gates 431a, 431b, 431c and 431d. The Key₄₁₀ bits 1110 are delivered as inputs to the respective XOR gates 431a, 431b, 431c and 431d. The encrypted value 0110 from the semiconductor chip 405 is delivered on a per bit basis as the other inputs to the XOR gates 431a, 431b, 431c and 431d. The XOR gates 431a, 431b, 431c and 431d perform the following XOR operations

$$0110 \oplus 1110 = 1000 \quad (5)$$

on a per bit basis as was described for the XOR operations performed by the XOR gates 427a, 427b, 427c and 427d. That value 1000 from Equation (5) constitutes Data Received by the semiconductor chip 410. The value 0010 sent from the semiconductor chip 405 is intended for the consumption of the semiconductor chip 415 only. Since the value 0010 has been transformed into the value 1000, the semiconductor chip 410 only sees the encrypted value 1000, not the true value 0010. Thus, the outputs of the XOR gates 431a, 431b, 431c and 431d are 1000 as shown at the inputs to the TFETs 340a, 340b, 340c and 340d, respectively. The gate control circuit 330 is outputting a logic 1 HIGH signal so the TFETs 340a, 340b, 340c and 340d are turned on and the encrypted value 1000 is passed to the semiconductor chip 415.

The semiconductor chip 415 includes the 4-bit encryption key Key₄₁₅ and four XOR gates 436a, 436b, 436c and 436d. The Key₄₁₅ bits 1010 are delivered as inputs to the respective XOR gates 436a, 436b, 436c and 436d. The encrypted value 1000 from the semiconductor chip 410 is delivered on a per bit basis as the other inputs to the XOR gates 436a, 436b, 436c and 436d. The XOR gates 436a, 436b, 436c and 436d perform the following XOR operations

$$1000 \oplus 1010 = 0010 \quad (6)$$

on a per bit basis as was described for the XOR operations performed by the XOR gates 427a, 427b, 427c and 427d. That value 0010 from Equation (6) is the original true value transmitted from the semiconductor chip 405 now decrypted and constitutes Data Received by the semiconductor chip 415. The value 0010 sent from the semiconductor chip 405 is intended for the consumption of the semiconductor chip 415 only. To keep the now decrypted value 0010 from being observable by the semiconductor chip 420, the gate control circuit 361, on instruction from the switching control logic

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block 290 of the semiconductor chip 405, turns off the TFETs 371a, 371b, 371c and 371d by swinging the gate input signals to logic LOW 0, thereby preventing the value 0010 from passing to the semiconductor chip 420. The outputs of the TFETs 371a, 371b, 371c and 371d will simply be logic LOW 0.

Of course, if the data value 0010 had been intended for consumption by the semiconductor chip 420 only, then the same types of XOR operations just described would be performed to encrypt and decrypt the true value 0010 for consumption by the semiconductor chip 420 using the Key₄₂₀ and the XOR gates 441a, 441b, 441c and 441d of the semiconductor chip 420. The gate control circuit 386, on instruction from the switching control logic block 290 of the semiconductor chip 405, turns off the TFETs 391a, 391b, 391c and 391d by swinging the gate input signals to logic LOW 0, thereby preventing a decrypted data value from passing beyond the semiconductor chip 420. Note that the foregoing data transmission can occur repeatedly for all sorts of data values and at speeds as fast or slow as the semiconductor chip architecture of the semiconductor chip stack 400 allows.

An alternate exemplary arrangement of a chip stack 500 that incorporates data compartmentalization, encryption and decryption may be understood by referring to FIG. 6. FIG. 6 is a sectional-like schematic view similar to FIG. 5 and depicts the semiconductor chip stack 500 with semiconductor chips 505, 510, 515, and 520. The semiconductor chips 505, 510, 515, and 520 share many of the same attributes as the semiconductor chips 205, 210, 215 and 220 depicted in FIG. 4 and described above. In this regard, the semiconductor chip to 505 includes the TFETs 255a, 255b, 255c and 255d as well as the interconnects 250, the switching control logic block 290 and the gate control network 292. The individual components of the gate control network 292 will not be shown in FIG. 6 for simplicity of illustration. The semiconductor chip 510 similarly includes the TFETs 340a, 340b, 340c and 340d, as well as the gate control network 330, which like the gate control network 292, will not include additional element numbering of the individual components for simplicity of illustration. The semiconductor chips 505 and 510 are electrically connected by way of the plural interconnects 310. Similar pluralities of the interconnects 310 connect the semiconductor chips 510 and 515 and 515 and 520, respectively. The semiconductor chip 515 similarly includes the TFETs 371a, 371b, 371c and 371d, as well as the gate control network 361. Finally, the semiconductor chip 520 includes the TFETs 391a, 391b, 391c and 391d as well as the gate control network 386.

Like the semiconductor chip stack 400 shown in FIG. 5, the exemplary semiconductor chip stack 500 depicted in FIG. 6 incorporates encryption schemes in order to encrypt data that is transferred from one chip to another. This illustrative encryption scheme will now be described. To simplify the discussion, a simple 4-bit data transmission scheme will be described. However, the skilled artisan will appreciate that other than 4-bit data can be handled with appropriate scaling up of the hardware to be described. The semiconductor chip 505 has an encryption circuit 522 that includes the Master exclusive OR (XOR) block 423 discussed above and a 4-bit encryption key Key₅₀₅, which can be identical to the Key₄₀₅ and shown in FIG. 5 and include four key bits 1111. However, in lieu of the four XOR gates 427a, 427b, 427c and 427d used in FIG. 5, the semiconductor chip 505 uses four inverters 555a, 555b, 555c and 555d as part of the encryption hardware. The outputs of the inverters 555a, 555b, 555c and 555d are tied to the inputs of

the TFETs **255a**, **255b**, **255c** and **255d**, respectively. The master XOR block **423** has four outputs, one for each of the inverters **555a**, **555b**, **555c** and **555d**. Note that the Key₅₀₅ bits 1111 are denoted in italics to distinguish them from the outputs of the master XOR block **423**. The semiconductor chip **510** includes a 4-bit Key₅₁₀ with four key bits 1110, the semiconductor chip **515** includes a 4-bit key Key₅₁₅ with key bits 1010 and the semiconductor chip **520** includes a 4-bit key Key₅₂₀ with key bits 0001. Table 4 below summarizes the key bits for the keys Key₅₀₅, Key₅₁₀, Key₅₁₅ and Key₅₂₀.

TABLE 4

Key	Key bits
Key ₅₀₅	Key ₅₀₅ bits = 1111
Key ₅₁₀	Key ₅₁₀ bits = 1110
Key ₅₁₅	Key ₅₁₅ bits = 1010
Key ₅₂₀	Key ₅₂₀ bits = 0001

The Key₅₀₅ bits 1111 are delivered as inputs to an AND block **557**. As described in more detail below, the AND block **557** consists of four AND gates, one for each key bit. Each of the AND gates has two inputs: one of the Key₅₀₅ key bits and the gate control signal from the gate control circuit **292**, which is in this illustration logic 1 HIGH. Thus when the gate control signal is logic 1 HIGH, the AND block **557** will output the Key₅₀₅ key bits 1111 as gate inputs to the TFETs **255a**, **255b**, **255c** and **255d**, respectively. Thus all the TFETs **255a**, **255b**, **255c** and **255d** will turn on and pass the outputs of the inverters **555a**, **555b**, **555c** and **555d**. When the gate control signal input to the AND block **557** is logic 0 LOW, the AND block **557** will output logic 0 LOW as gate inputs to the TFETs **255a**, **255b**, **255c** and **255d**, respectively, thereby turning them off and blocking the outputs of the inverters **555a**, **555b**, **555c** and **555d** from leaving the semiconductor chip **505**.

Assume for the purposes of this illustration that a 0010 data value is to be transmitted from the semiconductor chip **505** to the semiconductor chip **515**. The master XOR block **423** takes the input data value 0010 and performs XOR functions on that 0010 value to encrypt it into an encrypted 4-bit number that will be propagated through the semiconductor chip **510** and ultimately delivered to the semiconductor chip **515** where it will be decrypted back into the original data value 0010. Table 5 below lists the XOR operations performed by the XOR block **423** depending on the destination chip for the 0010 data value.

TABLE 5

Destination Chip	XOR Calculations
Chip 510	0010⊕Key ₅₀₅ bits⊕Key ₅₁₀ bits
Chip 515	0010⊕Key ₅₀₅ bits⊕Key ₅₁₀ bits⊕Key ₅₁₅ bits
Chip 520	0010⊕Key ₅₀₅ bits⊕Key ₅₁₀ bits⊕Key ₅₁₅ bits⊕Key ₅₂₀ bits

where again the ⊕ symbol denotes an XOR operation. Thus where the destination chip is the semiconductor chip **515**, the XOR calculations for the data value of 0010 and the key bits listed in Table 4 above are

$$0010 \oplus 1111 \oplus 1110 \oplus 1010 = 1001 \quad (6)$$

where the XOR calculations are done on a per bit basis. Take for example the first XOR calculation 0010⊕1111. Here the first bit, bit 0, of the data value 0010 is XORed with the first bit, bit 1, of the Key₅₀₅ bits, in other words 0⊕1, which yields

a value of 1. Next, the second bit, bit 0, of the data value 0010 is XORed with the second bit, bit 1, of the Key₅₀₅ bits, in other words 0⊕1, which yields a value of 1. Next, the third bit, bit 1, of the data value 0010 is XORed with the third bit, bit 1, of the Key₅₀₅ bits, in other words 1⊕1, which yields a value of 0 and so on for the last bit, bit 0, of the data value 0010 and the last bit, bit 1, of the Key₅₀₅ bits. Thus

$$0010 \oplus 1111 = 1101 \quad (7)$$

That value 1101 from Equation (7) is next XORed with the Key₅₁₀ key bits 1110 on the same bit per bit basis to yield

$$1101 \oplus 1110 = 0011 \quad (8)$$

and then that value 0011 is next XORed with the Key₅₁₅ key bits 1010 on the same bit per bit basis to yield

$$0011 \oplus 1010 = 1001 \quad (9)$$

which, of course, is the result for Equation (6). The bit values 1001 from Equations (6) and (9) are delivered as inputs to the inverters **555a**, **555b**, **555c** and **555d**. The inverters **555a**, **555b**, **555c** and **555d** then invert the bit values 1001 to 0110 and deliver those 0110 bits as inputs to the TFETs **255a**, **255b**, **255c** and **255d**, respectively, where they are passed along to respective inputs of inverters **563a**, **563b**, **563c** and **563d** of the semiconductor chip **510**.

The semiconductor chip **510** includes the 4-bit encryption key Key₅₁₀, an AND block **567** and the aforementioned inverters **563a**, **563b**, **563c** and **563d**. The 0110 bit values received from the TFETs **255a**, **255b**, **255c** and **255d** are input both to the inverters **563a**, **563b**, **563c** and **563d** and to an XOR block **569**. In addition, the Key₅₁₀ key bits 1110 are delivered as inputs to the XOR block **569**. As described in more detail below in conjunction with FIG. 8, the XOR block **569** consists of four XOR gates, one for each key bit. Each of the XOR gates has two inputs: one of the Key₅₁₀ key bits 1111 and one of the inputs to the inverters **563a**, **563b**, **563c** and **563d**. The XOR block **569** converts the 0110 bits input into Data Received bits 1000. But note that the Data Received bits 1000 does not match the original data 0010. This is by design, since the 0010 data was not intended to be viewable by the semiconductor chip **510**, but only the semiconductor chip **515**. Thus, from the point of view of the semiconductor chip **510**, the transmitted data is 1000, not the true data 0010. The inverters **563a**, **563b**, **563c** and **563d** invert the bit values 0110 received from the TFETs **255a**, **255b**, **255c** and **255d** to 1001 and deliver those 1001 bits as inputs to the TFETs **340a**, **340b**, **340c** and **340d**, respectively. Concurrently, the Key₅₁₀ bits 1110 are delivered as inputs to the AND block **567**. As described in more detail below in conjunction with FIG. 7, the AND block **567**, like the AND block **557** of semiconductor chip **505**, consists of four AND gates, one for each key bit. Each of the AND gates has two inputs: one of the Key₅₁₀ key bits and the gate control signal from the gate control circuit **330**, which is in this illustration is logic 1 HIGH. Thus when the gate control signal is logic 1 HIGH, the AND block **567** will output the Key₅₁₀ key bits 1110 as gate inputs to the TFETs **340a**, **340b**, **340c** and **340d**, respectively. Thus the TFETs **340a**, **340b** and **340c** will turn on and pass the outputs of the inverters **563a**, **563b** and **563c**, but the TFET **340d** will turn off and pass logic 0 LOW, so that the output of the inverter **563d** is not passed on. Thus, the TFETs **340a**, **340b**, **340c** and **340d** will pass bit values 1000 to inputs of inverters **573a**, **573b**, **573c** and **573d**, respectively, of the semiconductor chip **515**.

The semiconductor chip **515** includes the 4-bit encryption key Key₅₁₅, an AND block **577** and the aforementioned inverters **573a**, **573b**, **573c** and **573d**. The 1000 bit values

received from the TFETs **340a**, **340b**, **340c** and **340d** are input both to the inverters **573a**, **573b**, **573c** and **573d** and to an XOR block **579**. In addition, the Key₅₁₅ key bits 1010 are delivered as inputs to the XOR block **579**. The XOR block **579** consists of four XOR gates, one for each key bit. Each of the XOR gates has two inputs: one of the Key₅₁₅ key bits 1010 and one of the inputs to the inverters **573a**, **573b**, **573c** and **573d**. The XOR block **579** converts the 1000 bit values received from the TFETs **340a**, **340b**, **340c** and **340d** into Data Received bits 0010. Note that the Data Received bits 0010 do match the original data 0010 generated, encrypted and sent by the semiconductor chip **505**. This is by design, since the 0010 data was intended to be viewable by the semiconductor chip **515** only. Thus, from the point of view of the semiconductor chip **515**, the transmitted data is the true data 0010. The inverters **573a**, **573b**, **573c** and **573d** invert the bit values 1000 received from the TFETs **340a**, **340b**, **340c** and **340d** to 0111 and deliver those 0111 bits as inputs to the TFETs **371a**, **371b**, **371c** and **371d**, respectively. Concurrently, the Key₅₁₅ bits 1010 are delivered as inputs to the AND block **577**. As described in more detail below, the AND block **577**, like the AND block **557** of semiconductor chip **505**, consists of four AND gates, one for each key bit. Each of the AND gates has two inputs: one of the Key₅₁₅ key bits and the gate control signal from the gate control circuit **361**, which is in this illustration logic 0 LOW. Thus when the gate control signal is logic 0 LOW, the AND block **577** will output logic 0 LOW as gate inputs to the TFETs **371a**, **371b**, **371c** and **371d**, respectively. Thus the TFETs **371a**, **371b**, **371c** and **371d** will turn off and not pass the outputs of the inverters **573a**, **573b**, **573c** and **573d** to inputs of inverters **581a**, **581b**, **581c** and **581d** of the semiconductor chip **520**. In this way, the semiconductor chip **520** is prevented from seeing the outputs of the TFETs **371a**, **371b**, **371c** and **371d**. Of course, if the semiconductor chip **520** was the intended recipient of the transmitted data, then the gate control signal input to the AND block **577** would be logic 1 HIGH. Note that the foregoing data transmission can occur repeatedly for all sorts of data values and at speeds as fast or slow as the semiconductor chip architecture of the semiconductor chip stack **500** allows.

Although the semiconductor chip **520** was not the intended recipient of the transmitted data 0010 in this example, it could have been and therefore includes the same basic decryption features as the semiconductor chips **510** and **515**. In this regard, the semiconductor chip **520** includes the 4-bit encryption key Key₅₂₀, an AND block **584** and the aforementioned inverters **581a**, **581b**, **581c** and **581d**. Any bit values received from the TFETs **371a**, **371b**, **371c** and **371d** would be input both to the inverters **581a**, **581b**, **581c** and **581d** and to an XOR block **587**. In addition, the Key₅₂₀ key bits 0001 would be delivered as inputs to the XOR block **587**. The XOR block **587** consists of four XOR gates, one for each key bit. Each of the XOR gates has two inputs: one of the Key₅₂₀ key bits 0001 and one of the inputs to the inverters **581a**, **581b**, **581c** and **581d**. The XOR block **587** would convert the bit values received from the TFETs **371a**, **371b**, **371c** and **371d** into Data Received bits.

Additional details regarding the AND block **557** depicted in FIG. 6 will now be described in conjunction with FIG. 7, which is a schematic view. As noted above, the AND block **557** consists of four AND gates **603**, **606**, **609** and **612**. One input to each of the AND gates **603**, **606**, **609** and **612** is the gate control signal from the gate control circuit **292** shown in FIG. 6, and for the present discussion is logic 1 HIGH. The other input to each of the AND gates **603**, **606**, **609** and **612** is one of the Key₅₀₅ key bits 1111. The respective

outputs of the AND gates **603**, **606**, **609** and **612**, in this example, all logic 1 HIGH, are delivered to the inputs of the TFETs **255a**, **255b**, **255c** and **255d**. The foregoing description is applicable to the other AND blocks **567**, **577** and **584**, albeit with inputs of the appropriate key bits and outputs to the appropriate TFETs in a given chip.

Additional details regarding the XOR block **569** depicted in FIG. 6 will now be described in conjunction with FIG. 8, which is a schematic view. As noted above, the XOR block **569** consists of four XOR gates **617**, **619**, **624** and **628**. One input to each of the XOR gates **617**, **619**, **624** and **628** is the output from one of the TFETs **255a**, **255b**, **255c** and **255d**. The other input to each of the XOR gates **617**, **619**, **624** and **628** is one of the Key₅₁₀ key bits 1110. The respective outputs of the XOR gates **617**, **619**, **624** and **628**, in this example, the bit values 1000, constitutes the Data Received. The foregoing description is applicable to the other XOR blocks **579** and **587**, albeit with inputs of the appropriate key bits and the appropriate TFETs for a given chip.

An exemplary arrangement for the many TFETs disclosed herein can be understood by referring now to FIG. 9, which is a sectional view, and to FIG. 10, which is a plan view of the TFET **255a** of the semiconductor chip **205** depicted schematically in FIG. 4. In this regard, the TFET **255a** is implemented in the bulk semiconductor portion **245** and includes a gate electrode **711** that is a generally cylindrical shell structure with an internal bore **713** and composed of any of a variety of conductive materials, such as, for example, copper, aluminum, a laminate of ruthenium, tantalum nitride and ruthenium. The gate electrode **711** can include a conducting line **716** that extends laterally and can be connected to some overlying structure such as one of the interconnects **310** depicted in FIG. 4, for example. The gate electrode **711** traverses a semiconductor layer **722** but is electrically insulated therefrom by way of a liner insulating layer **729**, which can be composed of silicon oxide SiO_x. Note that the liner insulating layer **729** includes an upper sheet portion **731** which is formed on the upper surface of the semiconductor layer **722**. A transistor drain electrode **736** is formed also in a ring-like shape as more evident in FIG. 11 such that the gate electrode **711** is nested within the interior of the drain electrode **736** to leave a gap **737**. The drain electrode **736** can be composed of the same types of metallic materials used for the gate electrode **711**. The drain electrode **736** not only includes the conductor structure shown but also can include a conductor line **739** which can be used to connect to some overlying conductor structure such as one of the interconnects **310**. A drain **743** composed of a n+ type impurity region is formed in the semiconductor layer **722** by appropriate introduction of impurities such as n+ impurities, assuming that the semiconductor region **722** is a p-type silicon type layer. The source **747** of the transistor **255a** consists of a ring-like impurity region that is formed in the semiconductor layer **722** and can, like the drain **743**, consist of a n-type impurity region formed by the appropriate introduction of n-type impurities. Metallization contacts to the source **749** can be by way of an annular metal contact **751** which includes a projecting portion **753** that projects through an annular opening in the liner insulating layer **729** that is positioned beneath the source **747**. A photoresist layer **757** is positioned beneath the liner insulating layer **729** and includes an annular projection **766** that is designed to electrically insulate the gate electrode **711** from the electrical contact portion **751**. Note that the photoresist layer **757** has a central portion **769** that projects upwardly into the bore **713** of the gate electrode **711**. A bulk conductor pad or layer **772** is formed underneath the resist layer **757** and includes

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a projecting annular portion 776 that makes electrical contact with the annular contact 751. The gate electrode 711 includes a through via 777 that is lined with a liner portion 779 of the liner insulation layer 729. The through via 777 is used to connect to some underlying conductor structure, such as one of the gate control lines, say gate control line 285d shown in FIG. 4. The liner portion insulates the through via 777 from the bulk conductor pad 772. When the gate electrode 711 is swung HIGH, carriers (electrons) 782 flow in the channel region 786 surrounding the gate electrode 711 from the source 747 to the drain 743.

While the invention may be susceptible to various modifications and alternative forms, specific embodiments have been shown by way of example in the drawings and have been described in detail herein. However, it should be understood that the invention is not intended to be limited to the particular forms disclosed. Rather, the invention is to cover all modifications, equivalents and alternatives falling within the spirit and scope of the invention as defined by the following appended claims.

What is claimed is:

1. A semiconductor chip stack, comprising:
 - a first semiconductor chip comprising:
 - a first logic layer that includes a switching control logic block, first programmable elements, and second programmable elements; and
 - a first silicon layer on the first logic layer that includes: plural first through-silicon transistors connected to the switching control logic block through the second programmable elements and plural first through-silicon vias connected to the switching control logic block through the first programmable elements; and
 - a second semiconductor chip having plural second through-silicon transistors stacked on the first semiconductor chip, the second semiconductor chip configured to receive transmission of data from the plural first through silicon transistors and control signals from the plural first through-silicon vias,
 - wherein the first programmable elements are programmable to selectively pass transistor on or off signals to the plural first through-silicon transistors, and the second programmable elements are programmable to selectively pass the transistor on or off signals to the plural second through-silicon transistors of the second semiconductor chip.
 2. The semiconductor chip stack of claim 1, comprising a third semiconductor chip stacked on the second semiconductor chip, the second semiconductor chip including a second logic layer and a second silicon layer on the second logic layer, the second silicon layer having the plural second through-silicon transistors operable to selectively control a flow of data from the second semiconductor chip to the third semiconductor chip and having plural second through-silicon vias to convey control signals to the third semiconductor chip.
 3. The semiconductor chip stack of claim 1, wherein the plural first through-silicon transistors comprise through-silicon field effect transistors.
 4. The semiconductor chip stack of claim 1, wherein the switching control logic block is operable to deliver transistor on or off signals to the plural first through-silicon transistors and the plural second through-silicon transistors.
 5. The semiconductor chip stack of claim 1, wherein the plural second through-silicon transistors are through-silicon field effect transistors.

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6. The semiconductor chip stack of claim 1, wherein the first programmable elements and the second programmable elements comprise fuses or anti-fuses.

7. The semiconductor chip stack of claim 1, wherein the switching control logic block is operable to selectively pass transistor on or off signals through the first programmable elements but not through the second programmable elements.

8. The semiconductor chip stack of claim 4, wherein the switching control logic block is operable to selectively transmit transistor on or off signals through the first programmable elements but not through the second programmable elements.

9. An apparatus, comprising:

- a first semiconductor chip comprising:
 - a first logic layer that includes a switching control block, first programmable elements, and second programmable elements; and
 - a first silicon layer on the first logic layer that includes: plural first through-silicon transistors connected to the switching control logic block through the second programmable elements and plural first through-silicon vias connected to the switching control logic block through the first programmable elements; and
 - a second semiconductor chip having plural second through-silicon transistors stacked on the first semiconductor chip, the second semiconductor chip configured to receive transmission of data from the plural first through silicon transistors and control signals from the plural first through-silicon vias, wherein the first programmable elements are programmable to selectively pass transistor on or off signals to the plural first through-silicon transistors, and the second programmable elements are programmable to selectively pass the transistor on or off signals to the plural second through-silicon transistors of the second semiconductor chip, wherein the first semiconductor chip includes an encryption circuit operable to encrypt the data.

10. The apparatus of claim 9, wherein the plural first through-silicon transistors comprise through-silicon field effect transistors.

11. The apparatus of claim 9, wherein the switching control logic block is operable to deliver transistor on or off signals to the plural first through-silicon transistors and the second semiconductor chip.

12. The apparatus of claim 11, wherein the second programmable elements selectively pass the transistor on or off signals to second through-silicon vias.

13. The apparatus of claim 9, comprising the second semiconductor chip stacked on the first semiconductor chip.

14. A method of manufacturing, comprising:

- stacking a first semiconductor chip on a second semiconductor chip,
- the first semiconductor chip comprising:
 - a first logic layer that includes a switching control logic block, first programmable elements, and second programmable elements; and
 - a first silicon layer on the first logic layer that includes: plural first through-silicon transistors connected to the switching control logic block through the second programmable elements and plural first through-silicon vias connected to the switching control logic block through the first programmable elements; and

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the second semiconductor chip having plural second through-silicon transistors and configured to receive transmission of data from the plural first through silicon transistors and receive control signals from the plural first through-silicon vias, wherein the first programmable elements are programmable to selectively pass transistor on or off signals to the plural first through-silicon transistors, and the second programmable elements are programmable to selectively pass the transistor on or off signals to the plural second through-silicon transistors of the second semiconductor chip; and mounting the stacked semiconductor chips on a circuit board.

15. The method of claim 14, further comprising stacking a third semiconductor chip on the first semiconductor chip, the first semiconductor chip including a second logic layer and a second silicon layer on the second logic layer, the second silicon layer having the plural second through-silicon transistors operable to selectively control a flow of data from

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the first semiconductor chip to the third semiconductor chip and having plural second through-silicon vias to convey control signals to the third semiconductor chip.

16. The method of claim 14, wherein the plural first through-silicon transistors comprise through-silicon field effect transistors.

17. The method of claim 15, wherein the switching control logic block is operable to deliver transistor on or off signals to the plural first through-silicon transistors and to the plural second through-silicon transistors.

18. The method of claim 17, wherein the plural second through-silicon transistors comprise through-silicon field effect transistors.

19. The method of claim 18, wherein the first programmable elements and the second programmable elements comprise fuses or anti-fuses.

20. The method of claim 14, wherein the second semiconductor chip comprises an encryption circuit operable to encrypt the data.

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